1GB – 2x64Mx64 DDR2 SDRAM UNBUFFERED

FEATURES

- 240-pin, dual in-line memory module
- Fast data transfer rates: PC2-6400*, PC2-5300*, PC2-4200 and PC2-3200
- Utilizes 800*, 667*, 533 and 400 MT/s DDR2 SDRAM components
- V_{CC} = V_{CCQ} = 1.8V ±0.1V
- JEDEC standard 1.8V I/O (SSTL_18-compatible)
- Differential data strobe (DQS, DQS#) option
- Four-bit prefetch architecture
- Programmable CAS# latency (CL): 3, 4, 5 and 6
- On-die termination (ODT)
- Serial Presence Detect (SPD) with EEPROM
- Gold edge contacts
- Dual Rank
- RoHS compliant
- Package option
  - 240 Pin DIMM
  - PCB – 30.00mm (1.181") TYP

DESCRIPTION

The WV3HG264M64EEU is a 2x64Mx64 Double Data Rate DDR2 SDRAM high density module. This memory module consists of sixteen 64Mx8 bit with 4 banks DDR2 Synchronous DRAMs in FBGA packages, mounted on a 240-pin DIMM FR4 substrate.

* This product is under development, is not qualified or characterized and is subject to change or cancellation without notice.

NOTE: Consult factory for availability of:
- Vendor source control options
- Industrial temperature option

OPERATING FREQUENCIES

	PC2-3200	PC2-4200	PC2-5300*	PC2-6400*
Clock Speed	200MHz	266MHz	333MHz	400MHz
CL-t_{RCD}-t_{RP}	3-3-3	4-4-4	5-5-5	6-6-6

* Consult factory for availability

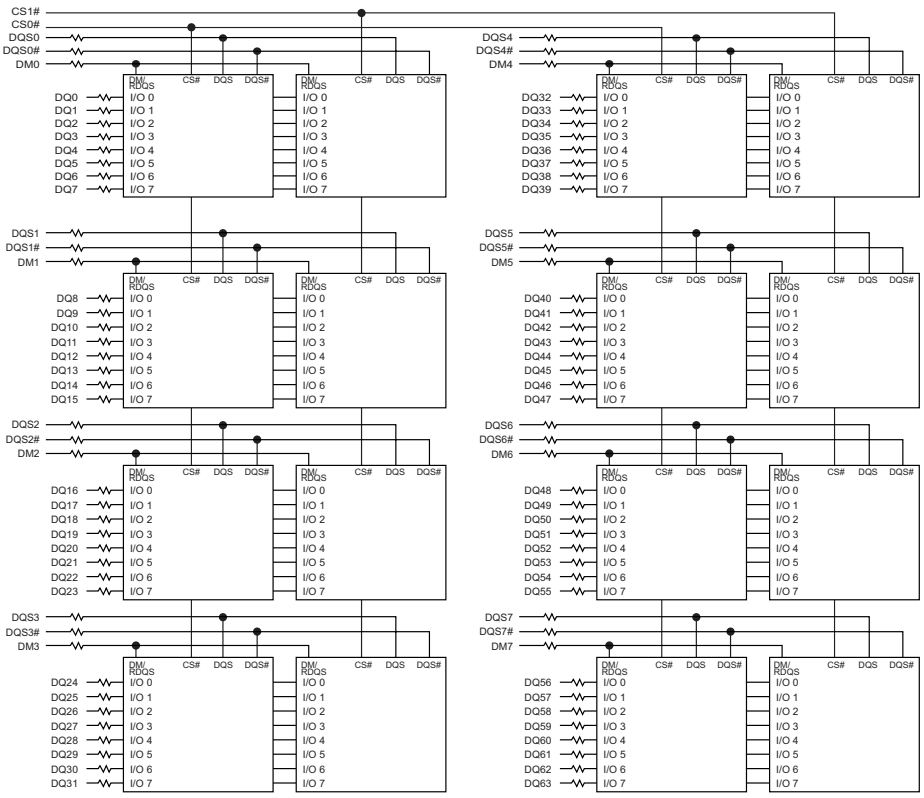
PIN CONFIGURATION

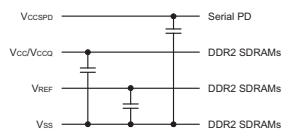
Pin No.	Symbol	Pin No.	Symbol	Pin No.	Symbol	Pin No.	Symbol
1	V_{REF}	61	A4	121	V_{SS}	181	V_{CCQ}
2	V_{SS}	62	V_{CCQ}	122	DQ4	182	A3
3	DQ0	63	A2	123	DQ5	183	A1
4	DQ1	64	V_{CC}	124	V_{SS}	184	V_{CC}
5	V_{SS}	65	V_{SS}	125	DM0	185	CK0
6	DQS0#	66	V_{SS}	126	NC	186	CK0#
7	DQS0	67	V_{CC}	127	V_{SS}	187	V_{CC}
8	V_{SS}	68	NC	128	DQ6	188	A0
9	DQ2	69	V_{CC}	129	DQ7	189	V_{CC}
10	DQ3	70	A10/AP	130	V_{SS}	190	BA1
11	V_{SS}	71	BA0	131	DQ12	191	V_{CCQ}
12	DQ8	72	V_{CCQ}	132	DQ13	192	RAS#
13	DQ9	73	WE#	133	V_{SS}	193	CS0#
14	V_{SS}	74	CAS#	134	DM1	194	V_{CCQ}
15	DQS1#	75	V_{CCQ}	135	NC	195	ODT0
16	DQS1	76	CS1#	136	V_{SS}	196	A13
17	V_{SS}	77	ODT1	137	CK1	197	V_{CC}
18	NC	78	V_{CCQ}	138	CK1#	198	V_{SS}
19	NC	79	V_{SS}	139	V_{SS}	199	DQ36
20	V_{SS}	80	DQ32	140	DQ14	200	DQ37
21	DQ10	81	DQ33	141	DQ15	201	V_{SS}
22	DQ11	82	V_{SS}	142	V_{SS}	202	DM4
23	V_{SS}	83	DQS4#	143	DQ20	203	NC
24	DQ16	84	DQS4	144	DQ21	204	V_{SS}
25	DQ17	85	V_{SS}	145	V_{SS}	205	DQ38
26	V_{SS}	86	DQ34	146	DM2	206	DQ39
27	DQS2#	87	DQ35	147	NC	207	V_{SS}
28	DQS2	88	V_{SS}	148	V_{SS}	208	DQ44
29	V_{SS}	89	DQ40	149	DQ22	209	DQ45
30	DQ18	90	DQ41	150	DQ23	210	V_{SS}
31	DQ19	91	V_{SS}	151	V_{SS}	211	DM5
32	V_{SS}	92	DQS5#	152	DQ28	212	NC
33	DQ24	93	DQS5	153	DQ29	213	V_{SS}
34	DQ25	94	V_{SS}	154	V_{SS}	214	DQ46
35	V_{SS}	95	DQ42	155	DM3	215	DQ47
36	DQS3#	96	DQ43	156	NC	216	V_{SS}
37	DQS3	97	V_{SS}	157	V_{SS}	217	DQ52
38	V_{SS}	98	DQ48	158	DQ30	218	DQ53
39	DQ26	99	DQ49	159	DQ31	219	V_{SS}
40	DQ27	100	V_{SS}	160	V_{SS}	220	CK2
41	V_{SS}	101	SA2	161	NC	221	CK2#
42	NC	102	NC	162	NC	222	V_{SS}
43	NC	103	V_{SS}	163	V_{SS}	223	DM6
44	V_{SS}	104	DQS6#	164	NC	224	NC
45	NC	105	DQS6	165	NC	225	V_{SS}
46	DQS8	106	V_{SS}	166	V_{SS}	226	DQ54
47	V_{SS}	107	DQ50	167	NC	227	DQ55
48	NC	108	DQ51	168	NC	228	V_{SS}
49	NC	109	V_{SS}	169	V_{SS}	229	DQ60
50	V_{SS}	110	DQ56	170	V_{CCQ}	230	DQ61
51	V_{CCQ}	111	DQ57	171	CKE1	231	V_{SS}
52	CKE0	112	V_{SS}	172	V_{CC}	232	DM7
53	V_{CC}	113	DQS7#	173	NC	233	NC
54	NC	114	DQS7	174	NC	234	V_{SS}
55	NC	115	V_{SS}	175	V_{CCQ}	235	DQ62
56	V_{CCQ}	116	DQ58	176	A12	236	DQ63
57	A11	117	DQ59	177	A9	237	V_{SS}
58	A7	118	V_{SS}	178	V_{CC}	238	V_{CCSPD}
59	V_{CC}	119	SDA	179	A8	239	SA0
60	A5	120	SCL	180	A6	240	SA1

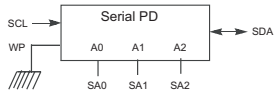
PIN NAMES

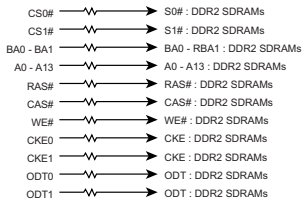
Pin Name	Function
A0-A13	Address Input
BA0, BA1	Bank Address
DQ0 ~ DQ63	Data Input/output
DQS0 ~ DQS7	Data Strobe
DQS0# ~ DQS7#	Data Strobe negative
ODT0, ODT1	On Die Termination
CK0,CK0# - CK2, CK2#	Clock Input
CKE0, CKE1	Clock enable input
CS0#, CS1#	Chip Select Input
RAS#	Row Address Strobe
CAS#	Column Address Strobe
WE#	Write Enable
V_{CC}	Voltage Supply (1.8V±0.1V)
V_{CCQ}	I/O Power (1.8V)
V_{SS}	Ground
SA0 ~ SA2	SPD Address
SDA	Serial Data I/O
SCL	Serial clock
DM(0-7)	Data Masks
A10/AP	Address input/Auto precharge
V_{REF}	I/O reference supply
V_{CCSPD}	Serial EEPROM
NC	No Connect

FUNCTIONAL BLOCK DIAGRAM









*Clock Wiring	
Clock Input	DDR2 SDRAMs
*CK0/CK0#	4 DDR2 SDRAMs
*CK1/CK1#	6 DDR2 SDRAMs
*CK2/CK2#	6 DDR2 SDRAMs

*Wire per Clock Loading Table/Wiring Diagrams

Notes:
1. DQ, DM, DQS, DQS# resistors: 5.1 Ohms +/- 5%
2. BAx, Ax, RAS#, CAS#, WE# resistors: 5.1 Ohms +/- 5%

NOTE: All resistor values are 22 ohms unless otherwise specified.

DC OPERATING CONDITIONS

All Voltages Referenced to V_{SS}

Parameter	Symbol	Rating			Units	Notes
		Min.	Type	Max.		
Supply Voltage	V_{CC}	1.7	1.8	1.9	V	1
I/O Supply Voltage	V_{CCQ}	1.7	1.8	1.9	V	4
VCCL Supply Voltage	V_{CCL}	1.7	1.8	1.9	V	4
I/O Reference Voltage	V_{REF}	0.49*V_{CCQ}	0.50*V_{CCQ}	0.51*V_{CCQ}	V	2
I/O Termination Voltage	V_{TT}	V_{REF}-0.04	V_{REF}	V_{REF}+0.04	V	3

Notes:

1. V_{CC} and V_{CCQ} must track each other. V_{CCQ} must be less than or equal to V_{CC}.
2. V_{REF} is expected to equal $V_{CCQ/2}$ of the transmitting device and to track variations in the DC level of the same. Peak-to-peak noise on V_{REF} may not exceed +/- percent of the DC value. Peak-to-peak AC noise on V_{REF} may not exceed +/-2 percent of V_{REF}. This measurement is to be taken at the nearest V_{REF} bypass capacitor.
3. V_{TT} is not applied directly to the device. V_{TT} is a system supply for signal termination resistors, is expected to be set equal to V_{REF} and must track variations in the DC level of V_{REF}.
4. V_{CCQ} tracks with V_{CC}; V_{CCL} track with V_{CC}.

ABSOLUTE MAXIMUM RATINGS

SSTL_1.8V

Symbol	Parameter		Min	Max	Unit
V_{CC}	Voltage on V_{CC} pin relative to V_{SS}		- 1.0	2.3	V
V_{CCQ}	Voltage on V_{CCQ} pin relative to V_{SS}		- 0.5	2.3	V
V_{CCL}	Voltage on V_{CCL} pin relative to V_{SS}		- 0.5	2.3	V
V_{IN}, V_{OUT}	Voltage on any pin relative to V_{SS}		- 0.5	2.3	V
T_{STG}	Storage Temperature		-55	100	°C
T_{CASE}	Device operating Temperature		0	85	°C
I_L	Input leakage current; Any input 0V<V_{IN}<V_{CC}; V_{REF} input 0V<V_{IN}<<0.95; Other pins not under test = 0V	Command/Address, RAS#, CAS#, WE#	-80	80	uA
		CS#, CKE	-40	40	uA
		CK, CK#	-30	30	uA
		DM	-10	10	uA
I_{OZ}	Output leakage current; 0V<V_{OUT}<V_{CCQ}; DQs and ODT are disable	DQ, DQS, DQS#	-10	10	uA
I_{VREF}	V_{REF} leakage current; V_{REF} = Valid V_{REF} level		-32	32	uA

CAPACITANCE

T_A = 25°C, f = 1MHz, V_{CC} = V_{CCQ} = 1.8V

Parameter	Symbol	Min	Max	Units
Input Capacitance: (A0 ~ A13 , BA0 ~ BA1, RAS#, CAS#, WE#)	C_{IN1}	20	36	pF
Input Capacitance: (CKE0, CKE1), (ODT0, ODT1)	C_{IN2}	12	20	pF
Input Capacitance: (CS0#, CS1#)	C_{IN3}	12	20	pF
Input Capacitance: (CK0, CK0# ~ CK2, CK2#)	C_{IN4}	10	16	pF
Input Capacitance: (DM0 ~ DM7)	$C_{IN6\ (E6)}$	9	11	pF
	$C_{IN6\ (D5)}$	9	12	pF
Input Capacitance: (DQ0 ~ DQ63)	$C_{OUT1\ (E6)}$	9	11	pF
	$C_{OUT1\ (D5)}$	9	12	pF

OPERATING TEMPERATURE CONDITION

Parameter	Symbol	Rating	Units	Notes
Operating Temperature	TOPER	0ºC to 85ºC	ºC	1, 2

Notes:

1. Operating temperature is the case surface temperature on the center/top side of the DRAM. For the measurement conditions, please refer to JEDEC JESD51.2.
2. At 0 - 85ºC, operation temperature range, all DRAM specification will be supported.

INPUT DC LOGIC LEVEL

All voltages referenced to V_{SS}

Parameter	Symbol	Min	Max	Units
Input High (Logic 1) Voltage	$V_{IH(DC)}$	VREF + 0.125	VREF + 0.300	V
Input Low (Logic 0) Voltage	$V_{IL(DC)}$	-0.300	VREF - 0.125	V

INPUT AC LOGIC LEVEL

All voltages referenced to V_{SS}

Parameter	Symbol	Min	Max	Units
AC Input High (Logic 1) Voltage	$V_{IH(AC)}$	VREF+ 0.250		V
AC Input Low (Logic 0) Voltage DDR2-400 & DDR2-533	$V_{IL(AC)}$		VREF - 0.250	V
AC Input Low (Logic 0) Voltage DDR2-667, DDR2-800 (TBD)	$V_{IL(AC)}$		VREF - 0.200	V

DDR2 I_{CC} SPECIFICATIONS AND CONDITIONS

Symbol	Proposed Conditions		806	665	534	403	Units
I_{CC0}*	Operating one bank active-precharge current; $t_{CK} = t_{CK}(I_{CC})$, $t_{RC} = t_{RC}(I_{CC})$, $t_{RAS} = t_{RAS}min(I_{CC})$; CKE is HIGH, CS# is HIGH between valid commands; Address bus inputs are SWITCHING; Data bus inputs are SWITCHING		TBD	744	704	704	mA
I_{CC1}*	Operating one bank active-read-precharge current; I_{OUT} = 0mA; BL = 4, CL = CL(I_{CC}), AL = 0; $t_{CK} = t_{CK}(I_{CC})$, $t_{RC} = t_{RC}(I_{CC})$, $t_{RAS} = t_{RAS\ MIN}(I_{CC})$, $t_{RCD} = t_{RCD}(I_{CC})$; CKE is HIGH, CS# is HIGH between valid commands; Address bus inputs are SWITCHING; Data pattern is same as I_{CC4W}		TBD	864	824	824	mA
I_{CC2P}**	Precharge power-down current; All banks idle; $t_{CK} = t_{CK}(I_{CC})$; CKE is LOW; Other control and address bus inputs are STABLE; Data bus inputs are FLOATING		TBD	128	128	128	mA
I_{CC2Q}**	Precharge quiet standby current; All banks idle; $t_{CK} = t_{CK}(I_{CC})$; CKE is HIGH, CS# is HIGH; Other control and address bus inputs are STABLE; Data bus inputs are FLOATING		TBD	560	480	480	mA
I_{CC2N}**	Precharge standby current; All banks idle; $t_{CK} = t_{CK}(I_{CC})$; CKE is HIGH, CS# is HIGH; Other control and address bus inputs are SWITCHING; Data bus inputs are SWITCHING		TBD	640	560	560	mA
I_{CC3P}**	Active power-down current; All banks open; $t_{CK} = t_{CK}(I_{CC})$; CKE is LOW; Other control and address bus inputs are STABLE; Data bus inputs are FLOATING	Fast PDN Exit MRS(12) = 0	TBD	480	480	480	mA
		Slow PDN Exit MRS(12) = 1	TBD	192	192	192	mA
I_{CC3N}**	Active standby current; All banks open; $t_{CK} = t_{CK}(I_{CC})$, $t_{RC} = t_{RC}(I_{CC})$, $t_{RAS} = t_{RAS\ MIN}(I_{CC})$; CKE is HIGH, CS# is HIGH between valid commands; Other control and address bus inputs are SWITCHING; Data bus inputs are SWITCHING		TBD	880	800	800	mA
I_{CC4W}**	Operating burst write current; All banks open, Continuous burst writes; BL = 4, CL = CL(I_{CC}), AL = 0; $t_{CK} = t_{CK}(I_{CC})$, $t_{RAS} = t_{RAS\ MAX}(I_{CC})$, $t_{RP} = t_{RP}(I_{CC})$; CKE is HIGH, CS# is HIGH between valid commands; Address bus inputs are SWITCHING; Data bus inputs are SWITCHING		TBD	1184	1024	944	mA
I_{CC4R}*	Operating burst read current; All banks open, Continuous burst reads, I_{OUT} = 0mA; BL = 4, CL = CL(I_{CC}), AL = 0; $t_{CK} = t_{CK}(I_{CC})$, $t_{RAS} = t_{RAS\ MAX}(I_{CC})$, $t_{RP} = t_{RP}(I_{CC})$; CKE is HIGH, CS# is HIGH between valid commands; Address bus inputs are SWITCHING; Data pattern is same as I_{CC4W}		TBD	1224	1064	944	mA
I_{CC5B}**	Burst auto refresh current; $t_{CK} = t_{CK}(I_{CC})$; Refresh command at every $t_{RFC}(I_{CC})$ interval; CKE is HIGH, CS# is HIGH between valid commands; Other control and address bus inputs are SWITCHING; Data bus inputs are SWITCHING		TBD	2400	2240	2240	mA
I_{CC6}*	Self refresh current; CK and CK# at 0V; CKE 0.2V; Other control and address bus inputs are FLOATING; Data bus inputs are FLOATING	Normal	TBD	128	128	128	mA
I_{CC7}*	Operating bank interleave read current; All bank interleaving reads, I_{OUT} = 0mA; BL = 4, CL = CL(I_{CC}), AL = $t_{RC}D(I_{CC})$-1*$t_{CK}(I_{CC})$; $t_{CK} = t_{CK}(I_{CC})$, $t_{RC} = t_{RC}(I_{CC})$, $t_{RRD} = t_{RRD}(I_{CC})$, t_{RCD} = 1*$t_{CK}(I_{CC})$; CKE is HIGH, CS# is HIGH between valid commands; Address bus inputs are STABLE during DESELECTs; Data bus inputs are switching.		TBD	1824	1824	1824	mA

* Value calculated as one module rank in thes operating condition, and all other module ranks in I_{CC2P} (CKE LOW) mode.

** Value calculated reflects all module ranks in this operating condition

NOTES:

- I_{CC} specifications were calculated using **SAMSUNG** components. Other manufactures DRAMs may have different values.

AC TIMING PARAMETERS

$0°C \le T_{CASE} < +85°C$; V_{CCQ} = + 1.8V ± 0.1V, V_{CC} = +1.8V ± 0.1V

AC CHARACTERISTICS				806		665		534		403		
PARAMETER			SYMBOL	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	UNIT
Clock	Clock cycle time	CL = 6	$t_{CK\ (6)}$	TBD	TBD							ps
		CL = 5	$t_{CK\ (5)}$	TBD	TBD	3000	8000					ps
		CL = 4	$t_{CK\ (4)}$	TBD	TBD	3750	8000	3,750	8,000	5,000	8,000	ps
		CL = 3	$t_{CK\ (3)}$	TBD	TBD	5680	8000	5,000	8,000	5,000	8,000	ps
	CK high-level width		t_{CH}	TBD	TBD	0.45	0.55	0.45	0.55	0.45	0.55	t_{CK}
	CK low-level width		t_{CL}	TBD	TBD	0.45	0.55	0.45	0.55	0.45	0.55	t_{CK}
	Half clock period		t_{HP}	TBD	TBD	MIN (t_{CH}, t_{CL})		MIN (t_{CH}, t_{CL})		MIN (t_{CH}, t_{CL})		ps
Data	DQ output access time from CK/CK#		t_{AC}	TBD	TBD	-450	+450	-500	+500	-600	+600	ps
	Data-out high-impedance window from CK/CK#		t_{HZ}	TBD	TBD		$t_{AC\ (MAX)}$		$t_{AC\ (MAX)}$		$t_{AC\ (MAX)}$	ps
	Data-out low-impedance window from CK/CK#		t_{LZ}	TBD	TBD	$t_{AC\ (MIN)}$	$t_{AC\ (MAX)}$	$t_{AC\ (MIN)}$	$t_{AC\ (MAX)}$	$t_{AC\ (MIN)}$	$t_{AC\ (MAX)}$	ps
	DQ and DM input setup time relative to DQS		t_{DS}	TBD	TBD	100		100		150		ps
	DQ and DM input hold time relative to DQS		t_{DH}	TBD	TBD	225		225		275		ps
	A DQ and DM input pulse width (for each input)		t_{DIPW}	TBD	TBD	0.35		0.35		0.35		t_{CK}
	Data hold skew factor		t_{QHS}	TBD	TBD		340		400		450	ps
	DQ…DQS hold, DQS to first DQ to go nonvalid, per access		t_{QH}	TBD	TBD	t_{HP} - t_{QHS}		t_{HP} - t_{QHS}		t_{HP} - t_{QHS}		ps
	Data valid output window (DVW)		t_{DVW}	TBD	TBD	t_{QH} - t_{DQSQ}		t_{QH} - t_{DQSQ}		t_{QH} - t_{DQSQ}		ns
Data Strobe	DQS input high pulse width		t_{DQSH}	TBD	TBD	0.35		0.35		0.35		t_{CK}
	DQS input low pulse width		t_{DQSL}	TBD	TBD	0.35		0.35		0.35		t_{CK}
	DQS output access time from CK/CK#		t_{DQSCK}	TBD	TBD	-400	+400	-450	+450	-500	+500	ps
	DQS falling edge to CK rising … setup time		t_{DSS}	TBD	TBD	0.2		0.2		0.2		t_{CK}
	DQS falling edge from CK rising … hold time		t_{DSH}	TBD	TBD	0.2		0.2		0.2		t_{CK}
	DQS…DQ skew, DQS to last DQ valid, per group, per access		t_{DQSQ}	TBD	TBD		240		300		350	ps
	DQS read preamble		t_{RPRE}	TBD	TBD	0.9	1.1	0.9	1.1	0.9	1.1	t_{CK}
	DQS read postamble		t_{RPST}	TBD	TBD	0.4	0.6	0.4	0.6	0.4	0.6	t_{CK}
	DQS write preamble setup time		t_{WPRES}	TBD	TBD	0		0		0		ps
	DQS write preamble		t_{WPRE}	TBD	TBD	0.35		0.35		0.35		t_{CK}
	DQS write postamble		t_{WPST}	TBD	TBD	0.4	0.6	0.4	0.6	0.4	0.6	t_{CK}
	Write command to first DQS latching transition		t_{DQSS}	TBD	TBD	WL - 0.25	WL + 0.25	WL - 0.25	WL + 0.25	WL - 0.25	WL + 0.25	t_{CK}
	Address and control input pulse width for each input		t_{IPW}	TBD	TBD	0.6		0.6		0.6		t_{CK}

NOTE:

- AC specification is based on **SAMSUNG** components. Other DRAM manufactures specification may be different.

Continued on next page

AC TIMING PARAMETERS (cont'd)

0°C ≤ T_{CASE} < +85°C; V_{CCQ} = + 1.8V ± 0.1V, V_{CC} = +1.8V ± 0.1V

AC CHARACTERISTICS			806		665		534		403		
	PARAMETER	SYMBOL	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	UNIT
Command and Address	Address and control input setup time	t_{IS}	TBD	TBD	200		250		250		ps
	Address and control input hold time	t_{IH}	TBD	TBD	275		375		475		ps
	CAS# to CAS# command delay	t_{CCD}	TBD	TBD	2		2		2		t_{CK}
	ACTIVE to ACTIVE (same bank) command	t_{RC}	TBD	TBD	55		55		55		ns
	ACTIVE bank a to ACTIVE bank b command	t_{RRD}	TBD	TBD	7.5		7.5		7.5		ns
	ACTIVE to READ or WRITE delay	t_{RCD}	TBD	TBD	15		15		15		ns
	Four Bank Activate period	t_{FAW}	TBD	TBD	37.5	37.5	37.5	37.5	37.5	37.5	
	ACTIVE to PRECHARGE command	t_{RAS}	TBD	TBD	45	70,000	45	70,000	45	70,000	ns
	Internal READ to precharge command delay	t_{RTP}	TBD	TBD	7.5		7.5		7.5		ns
	Write recovery time	t_{WR}	TBD	TBD	15		15		15		ns
	Auto precharge write recovery + precharge time	t_{DAL}	TBD	TBD	t_{WR} + t_{RP}		t_{WR} + t_{RP}		t_{WR} + t_{RP}		ns
	Internal WRITE to READ command delay	t_{WTR}	TBD	TBD	10		7.5		10		ns
	PRECHARGE command period	t_{RP}	TBD	TBD	15		15		15		
	PRECHARGE ALL command period	t_{RPA}	TBD	TBD	t_{WR} + t_{CK}		t_{WR} + t_{CK}		t_{WR} + t_{CK}		ns
	LOAD MODE command cycle time	t_{MRD}	TBD	TBD	2		2		2		t_{CK}
	CKE low to CK,CK# uncertainty	t_{DELAY}	TBD	TBD	t_{IS} + t_{CK} + t_{IH}		t_{IS} + t_{CK} + t_{IH}		t_{IS} + t_{CK} + t_{IH}		ns
Refresh	REFRESH to REFRESH command interval	t_{RFC}	TBD	TBD	127.5	127.5	127.5	70,000	127.5	70,000	ns
	Average periodic refresh interval	t_{REFI}	TBD	TBD		7.8		7.8		7.8	µs
Self Refresh	Exit self refresh to non-READ command	t_{XSNR}	TBD	TBD	t_{RFC} (MIN) + 10		t_{RFC} (MIN) + 10		t_{RFC} (MIN) + 10		ns
	Exit self refresh to READ command	t_{XSRD}	TBD	TBD	200		200		200		t_{CK}
	Exit self refresh timing reference	t_{ISXR}	TBD	TBD	t_{IS}		t_{IS}		t_{IS}		ps
ODT	ODT turn-on delay	t_{AOND}	TBD	TBD	2	2	2	2	2	2	t_{CK}
	ODT turn-on	t_{AON}	TBD	TBD	t_{AC} (MIN)	t_{AC} (MAX) + 1000	t_{AC} (MIN)	t_{AC} (MAX) + 1000	t_{AC} (MIN)	t_{AC} (MAX) + 1000	ps
	ODT turn-off delay	t_{AOFD}	TBD	TBD	2.5	2.5	2.5	2.5	2.5	2.5	t_{CK}
	ODT turn-off	t_{AOF}	TBD	TBD	t_{AC} (MIN)	t_{AC} (MAX) + 600	t_{AC} (MIN)	t_{AC} (MAX) + 600	t_{AC} (MIN)	t_{AC} (MAX) + 600	ps
	ODT turn-on (power-down mode)	t_{AONPD}	TBD	TBD	t_{AC} (MIN) + 2000	2 x t_{CK} + t_{AC} (MAX) + 1000	t_{AC} (MIN) + 2000	2 x t_{CK} + t_{AC} (MAX) + 1000	t_{AC} (MIN) + 2000	2 x t_{CK} + t_{AC} (MAX) + 1000	ps
	ODT turn-off (power-down mode)	t_{AOFPD}	TBD	TBD	t_{AC} (MIN) + 2000	2.5 x t_{CK} + t_{AC} (MAX) + 1000	t_{AC} (MIN) + 2000	2.5 x t_{CK} + t_{AC} (MAX) + 1000	t_{AC} (MIN) + 2000	2.5 x t_{CK} + t_{AC} (MAX) + 1000	ps
	ODT to power-down entry latency	t_{ANPD}	TBD	TBD	2		3		3		t_{CK}
	ODT power-down exit latency	t_{AXPD}	TBD	TBD	8		8		8		t_{CK}
Power-Down	Exit active power-down to READ command, MR[bit12=0]	t_{XARD}	TBD	TBD	2		2		2		t_{CK}
	Exit active power-down to READ command, MR[bit12=1]	t_{XARDS}	TBD	TBD	7-AL		6 - AL		6 - AL		t_{CK}
	A Exit precharge power-down to any non-READ command.	t_{XP}	TBD	TBD	2		2		2		t_{CK}
	CKE minimum high/low time	t_{CKE}	TBD	TBD	3		3		3		t_{CK}

NOTE:

- AC specification is based on **SAMSUNG** components. Other DRAM manufactures specification may be different.

ORDERING INFORMATION FOR D6

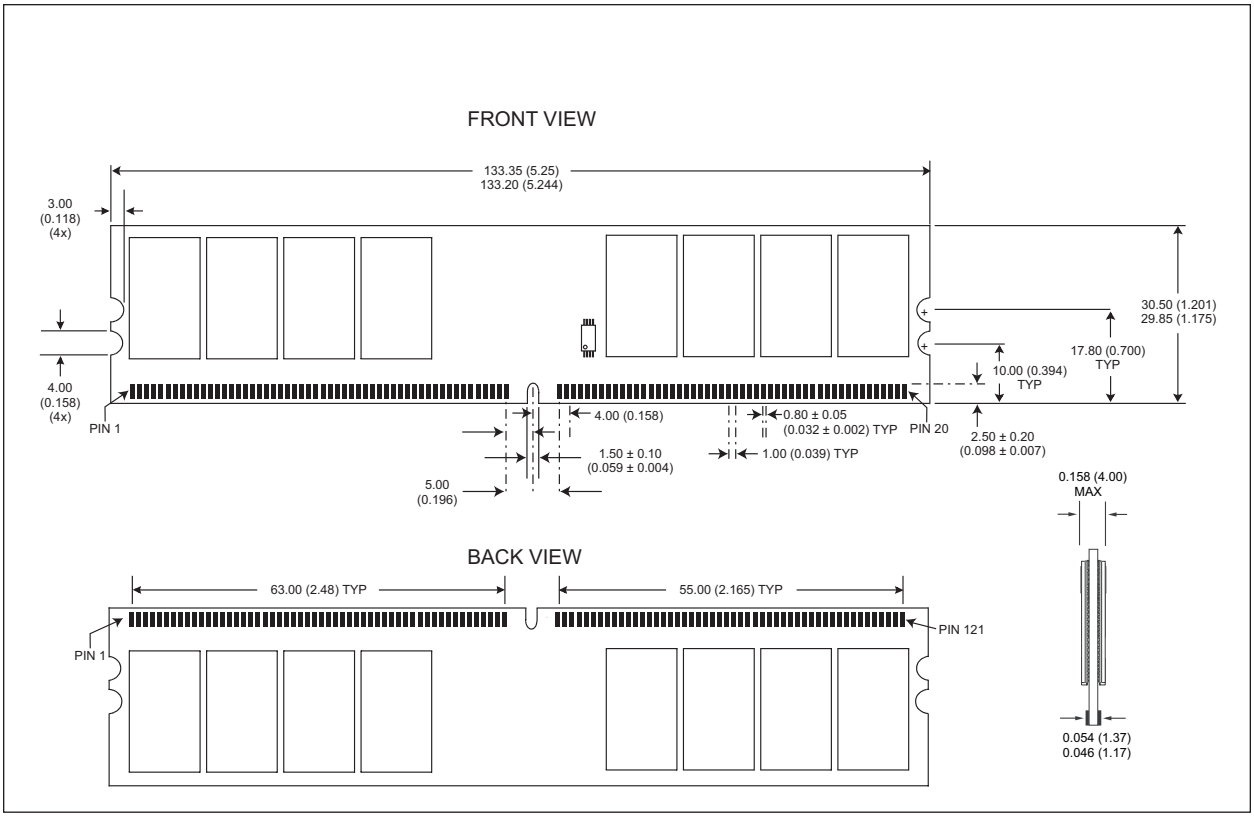
Part Number	Speed/Data Rate	CAS Latency	t_{RCD}	t_{RP}	Height*
WV3HG264M64EEU806D6xG**	400MHz/800Mb/s	6	6	6	30.00mm (1.181") TYP
WV3HG264M64EEU665D6xG**	333MHz/667Mb/s	5	5	5	30.00mm (1.181") TYP
WV3HG264M64EEU534D6xG	266MHz/533Mb/s	4	4	4	30.00mm (1.181") TYP
WV3HG264M64EEU403D6xG	200MHz/400Mb/s	3	3	3	30.00mm (1.181") TYP

** Consult factory for availability

NOTES:

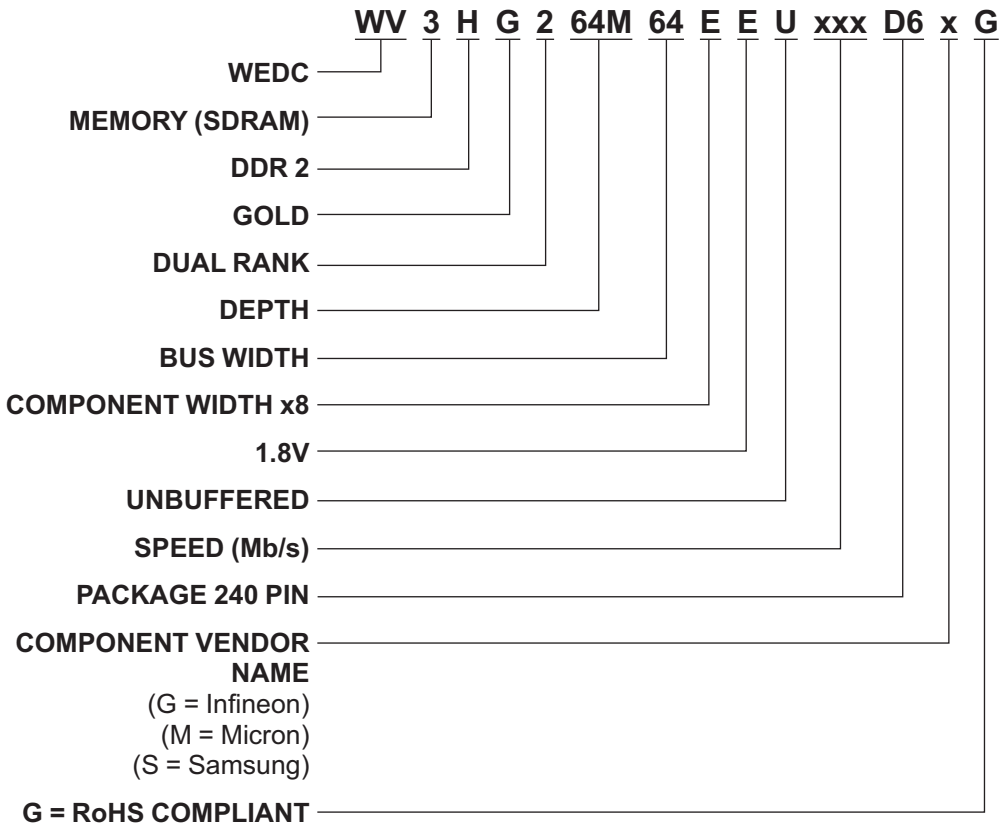
- RoHS compliant product. (G = RoHS Compliant)
- Vendor specific part numbers are used to provide memory component source control. The place holder for this is shown as a lower case "x" in the part numbers above and is to be replaced with respective vendors code. Consult factory for qualified sourcing options. (G = Infineon, M = Micron, S = Samsung & consult factory for others)
- Consult factory for availability of industrial temperature (-40°C to 85°C) option

PACKAGE DIMENSIONS FOR D6



* ALL DIMENSIONS ARE IN MILLIMETERS AND (INCHES)

PART NUMBERING GUIDE



Document Title

1GB – 2x64Mx64 DDR2 SDRAM UNBUFFERED

Revision History

Rev #	History	Release Date	Status
Rev 0	Created	December 2005	Advanced